



## Description

The DMP2010UFV-7 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

## General Features

$V_{DS} = -20V$   $I_D = -60A$

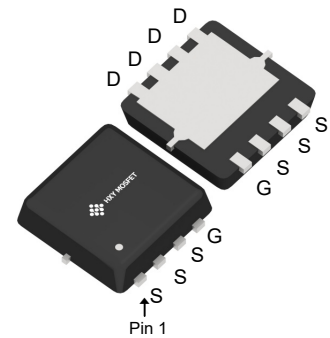
$R_{DS(ON)} < 10\text{ m}\Omega$  @  $V_{GS} = -4.5V$

## Application

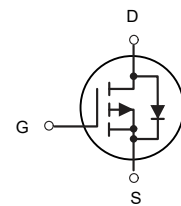
Battery protection

Load switch

Uninterruptible power supply



DFN3X3-8L



P-Channel MOSFET

## Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
DMP2010UFV-7	DFN3X3-8L	HXY MOSFET	5000

## Absolute Maximum Ratings ( $T_C = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	-20	V
$V_{GS}$	Gate-Source Voltage	$\pm 12$	V
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	-60	A
$I_D @ T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	-30	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	-78	A
$P_D @ T_C = 25^\circ\text{C}$	Total Power Dissipation <sup>4</sup>	22	W
TSTG	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance Junction-ambient <sup>1</sup>	75	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	4.2	$^\circ\text{C/W}$



**Electrical Characteristics ( $T_J=25^\circ\text{C}$ , unless otherwise noted)**

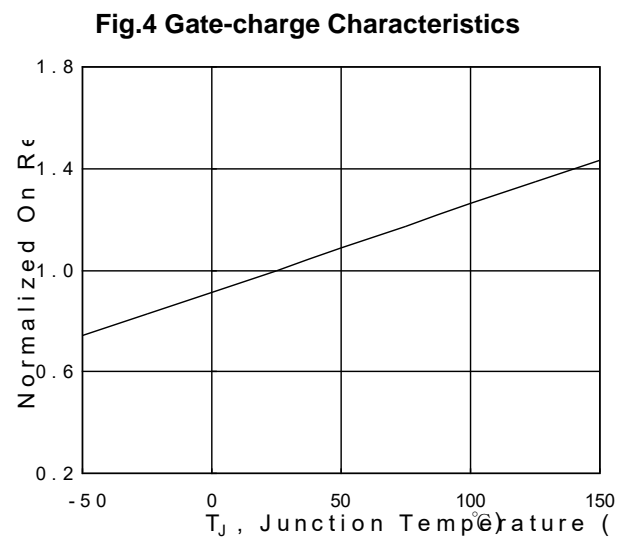
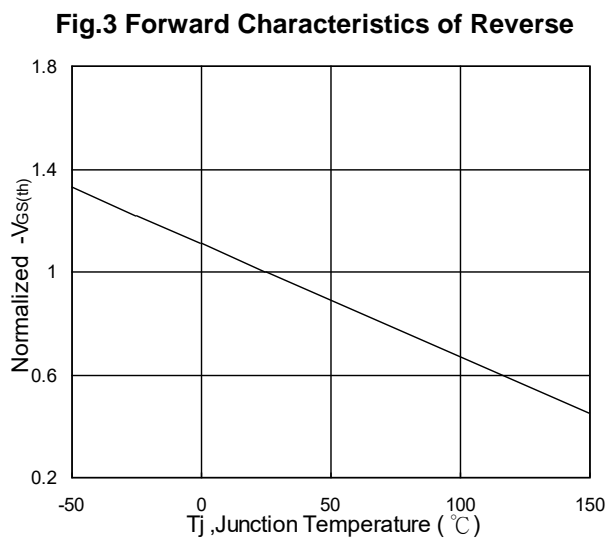
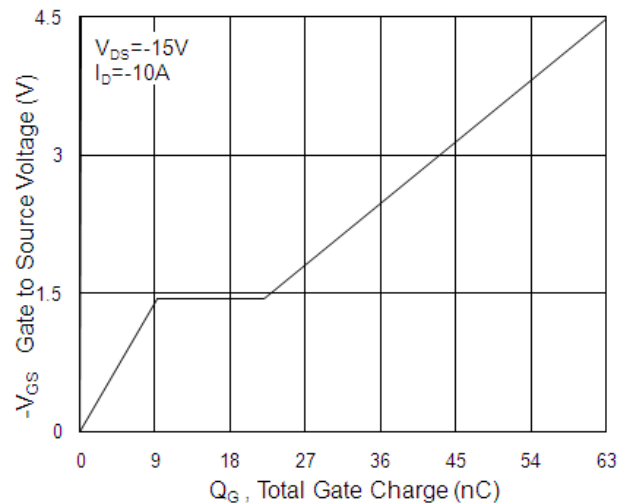
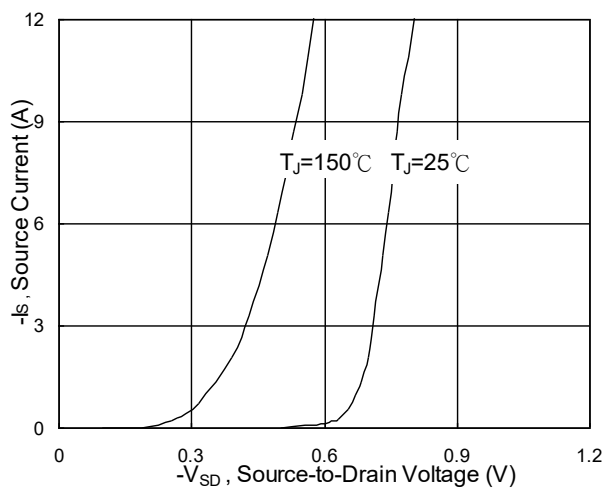
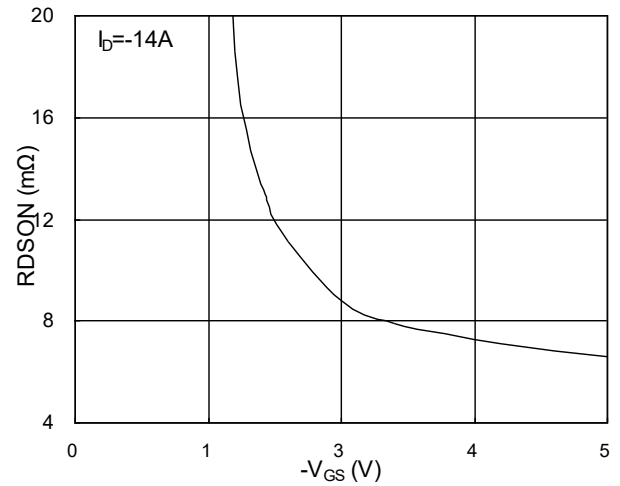
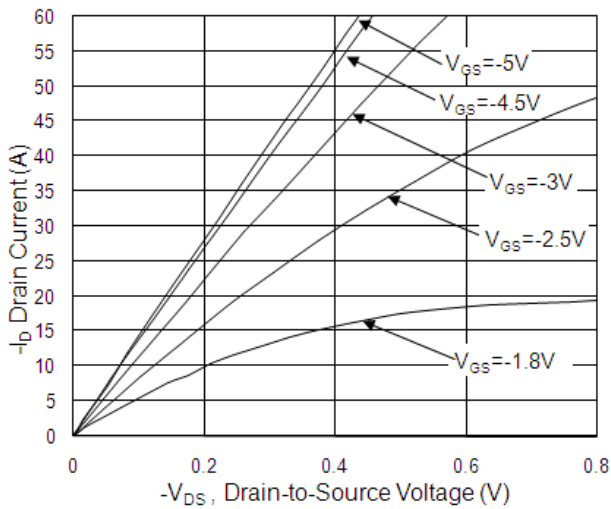
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V$ , $I_D=-250\mu A$	-20	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	$BV_{DSS}$ Temperature Coefficient	Reference to $25^\circ\text{C}$ , $I_D=-1mA$	---	-0.012	---	V/ $^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance <sup>2</sup>	$V_{GS}=-4.5V$ , $I_D=-10A$	---	7	10	m $\Omega$
		$V_{GS}=-2.5V$ , $I_D=-8A$	---	9	12	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$ , $I_D=-250\mu A$	-0.4	-0.7	-1.0	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	2.94	---	mV/ $^\circ\text{C}$
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS}=-15V$ , $V_{GS}=0V$ , $T_J=25^\circ\text{C}$	---	---	1	$\mu A$
$I_{GSS}$	Gate-Source Leakage Current	$V_{GS}=\pm 12V$ , $V_{DS}=0V$	---	---	$\pm 100$	nA
$g_{fs}$	Forward Transconductance	$V_{DS}=-5V$ , $I_D=-10A$	---	43	---	S
$Q_g$	Total Gate Charge (-4.5V)	$V_{DS}=-10V$ , $V_{GS}=-4.5V$ , $I_D=-10A$	---	35	---	nC
$Q_{gs}$	Gate-Source Charge		---	5.0	---	
$Q_{gd}$	Gate-Drain Charge		---	10	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=-10V$ , $V_{GS}=-4.5V$ , $R_G=3.3\Omega$ , $I_D=-10A$	---	12.0	---	ns
$T_r$	Rise Time		---	40.0	---	
$T_{d(off)}$	Turn-Off Delay Time		---	30	---	
$T_f$	Fall Time		---	10	---	
$C_{iss}$	Input Capacitance	$V_{DS}=-15V$ , $V_{GS}=0V$ , $f=1MHz$	---	2800	---	pF
$C_{oss}$	Output Capacitance		---	690	---	
$C_{rss}$	Reverse Transfer Capacitance		---	590	---	
$I_S$	Continuous Source Current <sup>1,4</sup>	$V_G=V_D=0V$ , Force Current	---	---	-60.0	A
$I_{SM}$	Pulsed Source Current <sup>2,4</sup>		---	---	---	A
$V_{SD}$	Diode Forward Voltage <sup>2</sup>	$V_{GS}=0V$ , $I_S=-1A$ , $T_J=25^\circ\text{C}$	---	---	-1.2	V
$t_{rr}$	Reverse Recovery Time	$I_F=-10A$ , $dI/dt=100A/\mu s$ ,	---	27	---	nS
$Q_{rr}$	Reverse Recovery Charge	$T_J=25^\circ\text{C}$	---	17.8	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 20Z copper.
- 2.The data tested by pulsed , pulse width  $\leq 300\mu s$  , duty cycle  $\leq 2\%$
- 3.The power dissipation is limited by  $150^\circ\text{C}$  junction temperature
- 4.The data is theoretically the same as  $I_D$  and  $I_{DM}$  , in real applications , should be limited by total power dissipation.



## Typical Characteristics



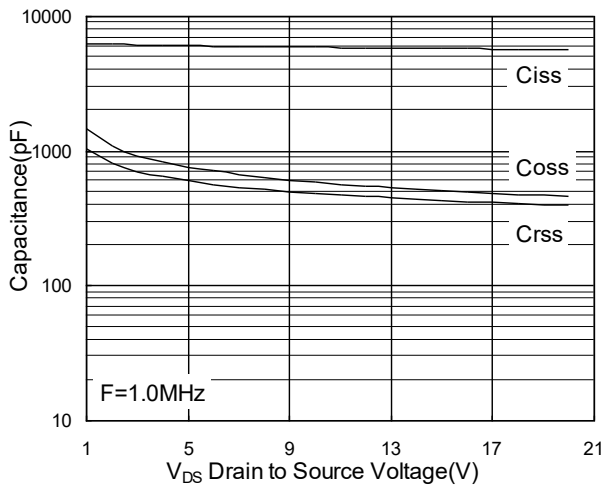


Fig.7 Capacitance

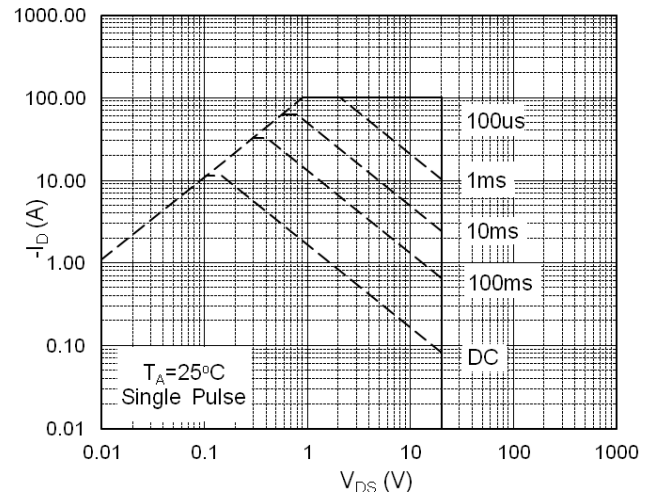


Fig.8 Safe Operating Area

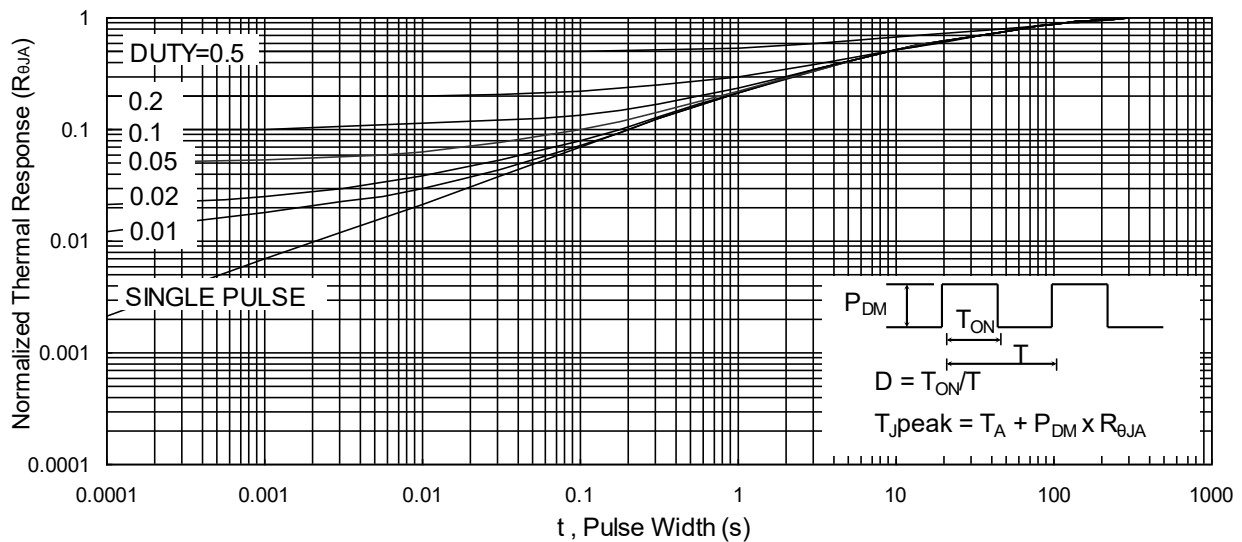


Fig.9 Normalized Maximum Transient Thermal Impedance

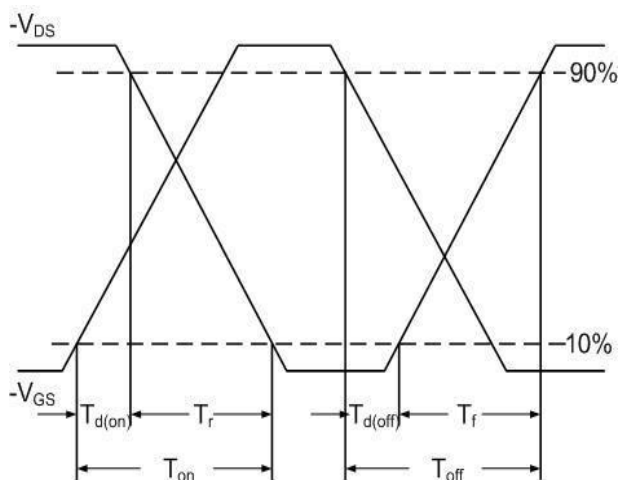


Fig.10 Switching Time Waveform

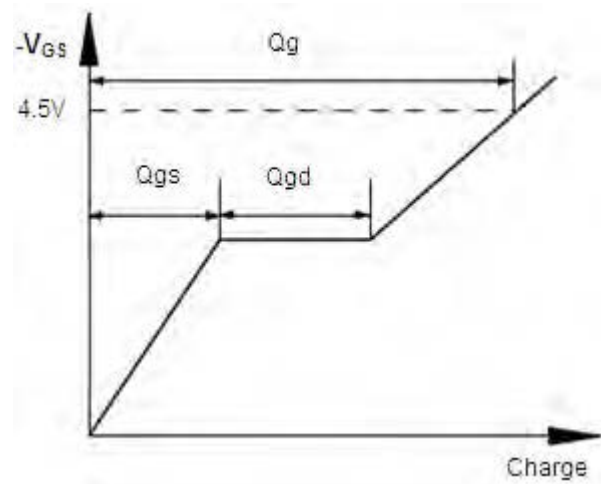
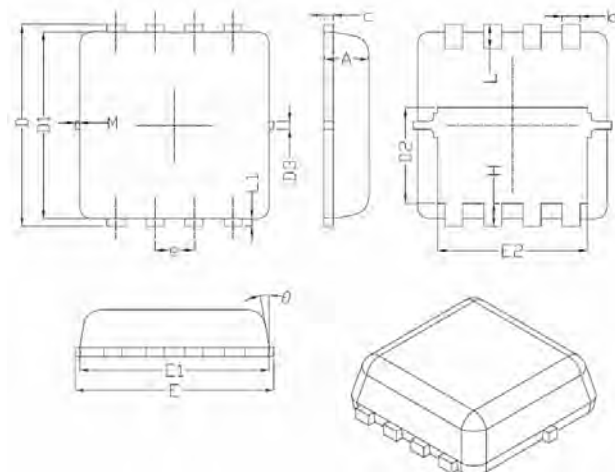


Fig.11 Gate Charge Waveform



## DFN3X3-8L Package Information



Symbol	Dimensions In Millimeters		
	Min.	Nom.	Max.
A	0.70	0.75	0.80
b	0.25	0.30	0.35
c	0.10	0.15	0.25
D	3.25	3.35	3.45
D1	3.00	3.10	3.20
D2	1.48	1.58	1.68
D3	-	0.13	-
E	3.20	3.30	3.40
E1	3.00	3.15	3.20
E2	2.39	2.49	2.59
e	0.65BSC		
H	0.30	0.39	0.50
L	0.30	0.40	0.50
L1	-	0.13	-
M	*	*	0.15
θ		10°	12°



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